



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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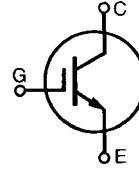


HiPerFAST™ IGBT with Diode Lightspeed™ Series

IXGA 7N60CD1
IXGP 7N60CD1

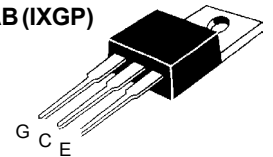
$V_{CES} = 600 \text{ V}$
 $I_{C25} = 14 \text{ A}$
 $V_{CE(sat)typ} = 2.0 \text{ V}$
 $t_{fi} = 45 \text{ ns}$

Preliminary Data

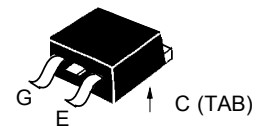


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	14	A
I_{C90}	$T_C = 90^\circ\text{C}$	7	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	30	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 300 \mu\text{H}$	$I_{CM} = 14$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	75	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque, (TO-220)	M3 M3.5	0.45/4 Nm/lb.in. 0.55/5 Nm/lb.in.
Weight	TO-220 TO-263	4 2	g g

TO-220AB (IXGP)



TO-263 AA (IXGA)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages
JEDEC TO-263 surface mountable and JEDEC TO-220 AB
- High frequency IGBT
- High current handling capability
- HiPerFAST™ HDMOS™ process
- MOS Gate turn-on
- drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

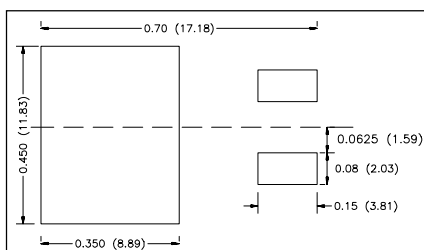
Advantages

- High power density
- Suitable for surface mounting
- Very low switching losses for high frequency applications

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			100 μA 750 μA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$	2.0	2.5	V

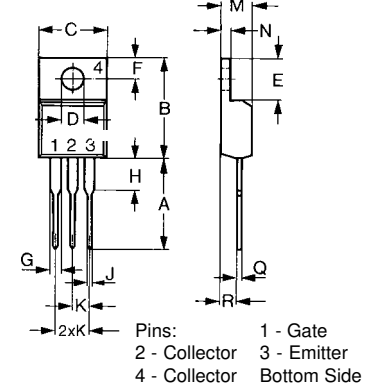
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	3	7	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		500	pF
C_{oes}			50	pF
C_{res}			17	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		25	nC
Q_{ge}			15	nC
Q_{gc}			10	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$ $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = R_{off} = 18\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		10	ns
t_{ri}			10	ns
$t_{d(off)}$			65	130 ns
t_{fi}			45	110 ns
E_{off}			0.12	0.25 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$ $V_{CE} = 0.8 \cdot V_{CES}$, $R_G = R_{off} = 18\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		10	ns
t_{ri}			15	ns
E_{on}			0.15	mJ
$t_{d(off)}$			120	ns
t_{fi}			85	ns
E_{off}			0.22	mJ
R_{thJC}	IGBT			1.65 K/W
R_{thCK}			0.25	K/W

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = 10\text{ A}$; $T_{VJ} = 150^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$			1.96 V 2.95 V
I_{RM}	$V_R = 100\text{ V}$; $I_F = 25\text{ A}$; $-di_F/dt = 100\text{ A}/\mu\text{s}$ $L < 0.05\text{ }\mu\text{H}$; $T_{VJ} = 100^\circ\text{C}$		2	2.5 V
t_{rr}	$I_F = 1\text{ A}$; $-di_F/dt = 50\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$; $T_J = 25^\circ\text{C}$		35	ns
R_{thJC}	Diode			1.6 K/W



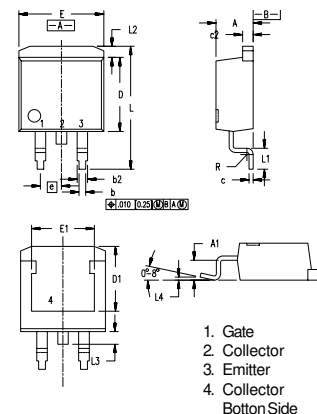
Min. Recommended Footprint
(Dimensions in inches and mm)

TO-220 AB Outline



Dim.	Millimeter	Inches
	Min.	Max.
A	12.70	13.97
B	14.73	16.00
C	9.91	10.66
D	3.54	4.08
E	5.85	6.85
F	2.54	3.18
G	1.15	1.65
H	2.79	5.84
J	0.64	1.01
K	2.54	BSC
M	4.32	4.82
N	1.14	1.39
Q	0.35	0.56
R	2.29	2.79

TO-263 AA Outline



Dim.	Millimeter	Inches
	Min.	Max.
A	4.06	4.83
A1	2.03	2.79
b	0.51	0.99
b2	1.14	1.40
c	0.46	0.74
c2	1.14	1.40
D	8.64	9.65
D1	7.11	8.13
E	9.65	10.29
E1	6.86	8.13
e	2.54	BSC
L	14.61	15.88
L1	2.29	2.79
L2	1.02	1.40
L3	1.27	1.78
L4	0	0.38
R	0.46	0.74

IXYS reserves the right to change limits, test conditions, and dimensions.